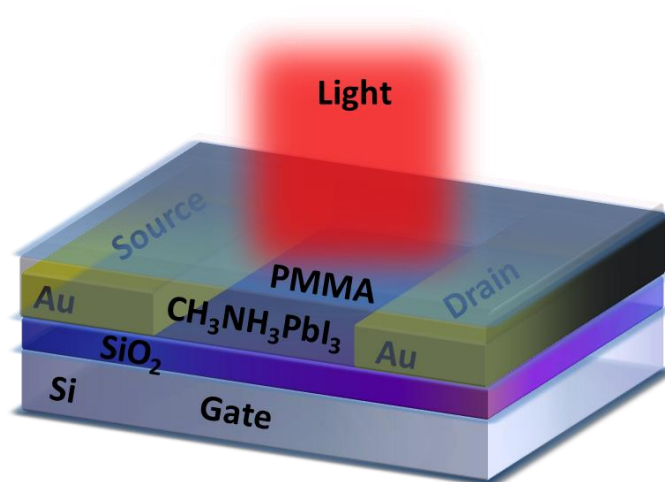
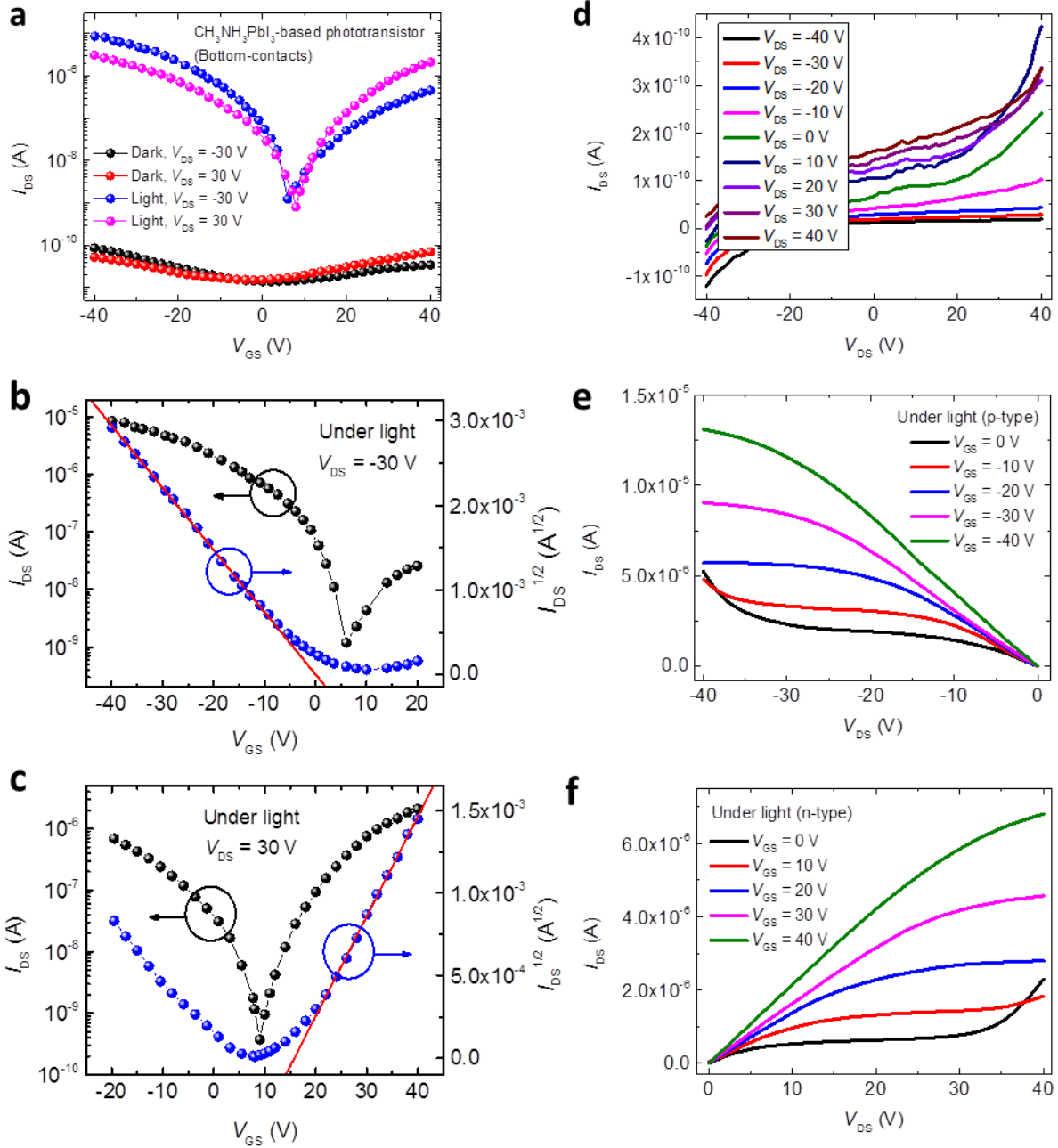


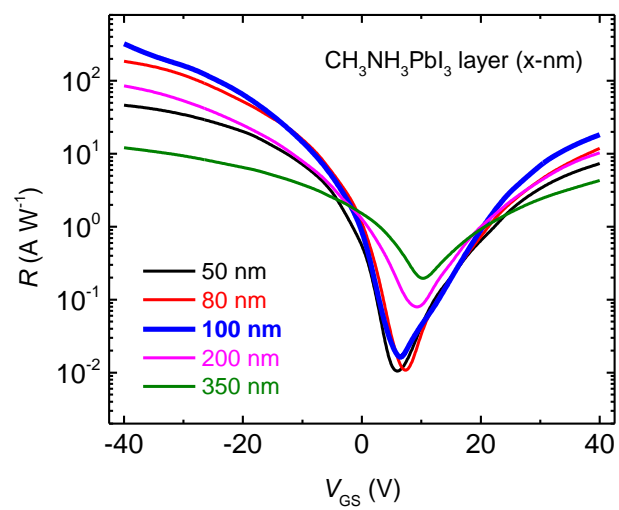
**Supplementary Figure 1. Film thickness measurement.** (a) AFM images of the perovskite film with a straight edge which was created by scratching with a tweezer. (b) Profile along the line highlighted in (a). This profile was used to estimate the thickness of the perovskite film.



**Supplementary Figure 2. Device schematic.** Schematic diagram for a CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub>-based phototransistor with the bottom-gate bottom-contact structure.

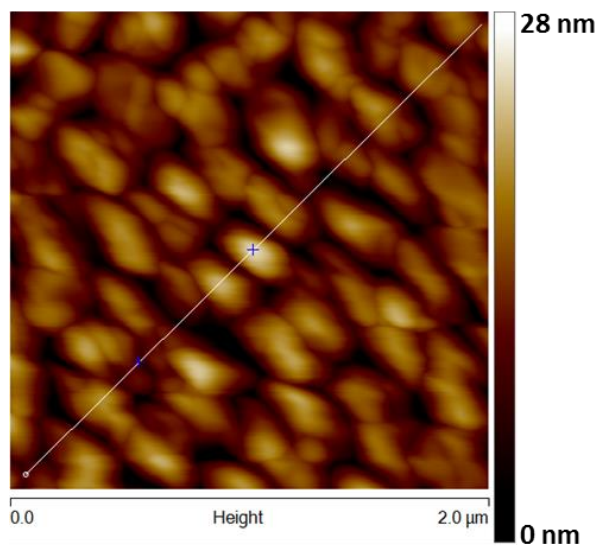


**Supplementary Figure 3. Performance of the bottom-gate, bottom-contact perovskite phototransistors. (a)** Transfer curves for the bottom-gate, bottom-contact phototransistor device. **(b)** and **(c)** represent, respectively, the transfer characteristics of p-type behavior and n-type behavior. **(d)**, **(e)** and **(f)** are output curves of the phototransistor in dark and under light illumination.

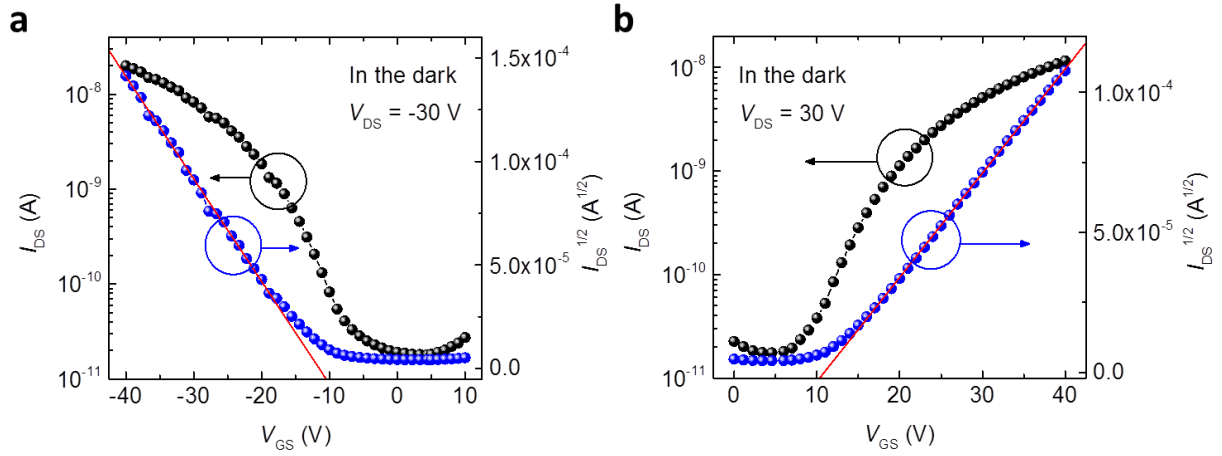


**Supplementary Figure 4. Photoresponsivity of the devices with various film thicknesses.**

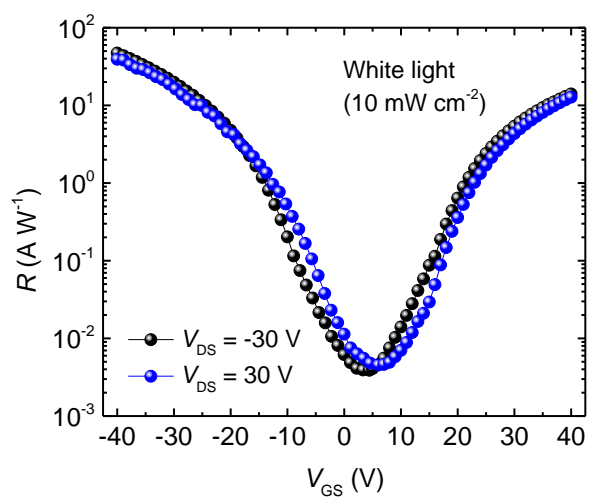
The device with a thickness of about 100 nm was found to present the optimal performance.



**Supplementary Figure 5. Atomic force microscopy (AFM) characterization of the  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  film surface.** The root-mean square roughness is approximately 8.95 nm, demonstrating a smoother surface compared to the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  film (shown in [Fig. 1d](#) in the main text).



**Supplementary Figure 6. Transfer curves of a hybrid perovskite  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ -based phototransistor in the dark.** (a) and (b) represent the transfer characteristics of a hybrid perovskite  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ -based phototransistor in the p-type and n-type regimes, respectively.



**Supplementary Figure 7. Photoresponsivity ( $R$ ) data.** Photoresponsivity ( $R$ ) measured on the perovskite CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub>-based phototransistor.

## Supplementary Table

**Supplementary Table 1. Performance of reported photodetectors based on hybrid perovskites.**

Ref.	Year	Materials	Configuration	Responsivity (A W <sup>-1</sup> )	Detectivity (Jones)	Response time
1	2014	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	solar cell	Photocurrent amplification > 100		
2	2014	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> /TiO <sub>2</sub> film	photodetector	0.49 × 10 <sup>-6</sup>		0.02 s
3	2014	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	photodetector	3.49		< 0.2 s
4	2014	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub> film	photodetector		~10 <sup>14</sup>	160 ns
5	2014	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> nanowires	phototransistor	5 × 10 <sup>-3</sup>		< 500 μs
6	2015	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	photodetector	14.5		0.2 μs
7	2015	Graphene- CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> composites	phototransistor	180	~10 <sup>9</sup>	87 ms
8	2015	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	photodetector	242		5.7 ± 1.0 μs
9	2015	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	photodiode		3 × 10 <sup>12</sup>	< 5 μs
10	2015	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	photodetector		7.4 × 10 <sup>12</sup>	120 ns
11	2015	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> film	optocoupler	1.0		20 μs
12	2015	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> nanowires	photodetector	1.3	2.5 × 10 <sup>12</sup>	0.3 ms



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